



# **Pin Configuration**

42-TQFN (ZH) Top-Side View



# **Pin Descriptions**

Pin#	Pin Name	Туре	Description
1, 2	AI+, AI-	Differential I/O	Differential I/O pair from PCIE signal source. Signal is routed to the AOa+, AOa- pin respectively when SEL=0. Signal is routed to the AOb+, AOb- pin respectively when SEL = 1.
37, 36	AOa+, AOa-	Differential I/O	Differential analog pass-through I/O. Signal from AI+ and AI- is routed to AOa+ and AOa- respectively when SEL=0.
3, 4	AOb+, AOb-	Differential I/O	Differential analog pass-through I/O. Signal from AI+ and AI- is routed to AOb+ and AOb- respectively when SEL=1.
5, 6	BI+, BI-	Differential I/O	Differential I/O pair from PCIE signal source. Signal is routed to the BOa+, BOa- pin respectively when SEL=0. Signal is routed to the BOb+, BOb- pin respectively when SEL = 1.
33, 32	BOa+, BOa-	Differential I/O	Differential analog pass-through I/O. Signal from BI+ and BI- is routed to BOa+ and BOa- respectively when SEL=0.
7, 8	BOb+, BOb-	Differential I/O	Differential analog pass-through I/O. Signal from BI+ and BI- is routed to BOb+ and BOb- respectively when SEL=1.
10, 11	CI+, CI-	Differential I/O	Differential I/O pair from PCIE signal source. Signal is routed to the COa+, COa- pin respectively When SEL=0. Signal is routed to the COb+, COb- pin respectively when SEL = 1.





# Pin Descriptions Cont.

Pin#	Pin Name	Туре	Description	
28, 27	COa+, COa-	Differential I/O	Differential analog pass-through I/O. Signal from CI+ and CI- is routed to COa+, COa- pin respectively when SEL = 0.	
12, 13	COb+, COb-	Differential I/O	Differential analog pass-through I/O. Signal from CI+ and CI- is routed to COb+, COb- pin respectively when SEL = 1.	
14, 15	DI+, DI-	Differential I/O	Differential I/O pair from PCIE signal source. Signal is routed to the DOa+, DOa- pin respectively when SEL=0. Signal is routed to the DOb+, DOb- pin respectively when SEL = 1.	
24, 23	DOa+, DOa-	Differential I/O	Differential analog pass-through I/O. Signal from DI+ and DI- is routed to DOa+, DOa- pin respectively when SEL = 0.	
16, 17	DOb+, DOb-	Differential I/O	Differential analog pass-through I/O. Signal from DI+ and DI- is routed to DOb+, DOb- pin respectively when SEL = 1.	
30	SEL	3.6V Tolerant Low-voltage Single-ended Input	SEL controls the mux through a flow-through latch.	
9, 19, 21, 26, 31, 34, 39, 41	VDD	Power Supply	Power, 3.3V ±10%	
18, 20, 22, 25, 29, 35, 38, 40, 42	GND	Power Supply	Power ground	

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## **Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	65°C to +150°C
Supply Voltage to Ground Potential	-0.5V to +3.7V
Channel DC Input Voltage	-0.5V to 1.5V
DC Output Current	
SEL DC Input Voltage	-0.5V to 3.7V
Junction Temperature	

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **Electrical Characteristics** Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>DD</sub>	3.3V Power Supply	—	3.0	3.3	3.6	V
I <sub>DD</sub>	Total Current from V <sub>DD</sub> 3.3V Supply	$SEL = 0V \text{ or } V_{DD}$	0	0.15	1	mA
T <sub>A</sub>	Operating Temperature Range	_	-40	_	85	°C

# **DC Electrical Characteristics** ( $T_A = -40^{\circ}C$ to $+85^{\circ}C$ , $V_{DD} = 3.3V \pm 10\%$ )

Parameter	Description	Test Conditions	Min.	Тур. <sup>(1)</sup>	Max.	Units
V <sub>IH-SEL</sub>	Input High Level, SEL Input	—	2.0	_	3.6	V
V <sub>IL-SEL</sub>	Input Low Level, SEL Input	_	0	—	0.8	V
I <sub>IN_SEL</sub>	Input Leakage Current, SEL Input	Measured with input at VIH-SEL max and VIL-SEL min	-10	_	10	μΑ
I <sub>IH</sub>	Input High Current, xI, xO	$V_{DD} = Max$ , $V_{IN} = 1.5V$	-10	_	10	μΑ
I <sub>IL</sub>	Input Low Current, xI, xO	$V_{DD} = Max$ , $V_{IN} = 0V$	-10	_	10	μΑ
I <sub>IH</sub>	Input High Current, SEL	$V_{DD} = Max$ , $V_{IN} = V_{DD}$	-5	_	5	μΑ
I <sub>IL</sub>	Input Low Current, SEL	$V_{DD} = Max, V_{IN} = 0V$	-5	_	5	μΑ
I <sub>OZH</sub>	HighZ High Current xOa, xOb	$V_{DD} = Max$ , $V_{IN} = 1.5V$	-10	_	10	μΑ
I <sub>OZL</sub>	HighZ Low Current xOa, xOb	$V_{DD} = Max, V_{IN} = 0V$	-10	_	10	μΑ

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Note:

1. Typical values are at V  $_{\rm DD}$  = 3.3V, T  $_{\rm A}$  = 25°C ambient and maximum loading.

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Parameter	Description	Test Conditions	Min	Typ (1)	Max	Units
				- <b>7</b> P·		
	Differential Insertion Loss	f = 50MHz - 1.25GHz		-0.8	-1.0	
DDIL		f = 1.25GHz - 2.5GHz		-1.1	-1.3	
		f = 2.5GHz - 4GHz		-1.2	-1.5	
		f = 5.0GHz		-1.7	-2.0	
			-25.8	-32.2	_	
DDIL <sub>OFF</sub>	Differential Off Isolation		-20.6	-25.8		- dB
		I = 0  to  4.0 GHZ	-17.6	-22.0		
			-15.4	-19.3		
DDRL	Differential Return Loss	f = 50MHz - 1.25GHz	-18.2	-22.7		
		f = 1.25GHz - 2.5GHz	-16.8	-21.0		
		f = 2.5GHz - 4GHz	-12	-15.0	_	
		f = 5.0GHz	-8	-10.0		
	Near End Crosstalk	f = 50MHz -1.25GHz	-44.8	-56		
DDNEXT		f = 1.25GHz - 2.5GHz	-41.6	-52	_	
		f = 2.5GHz - 4GHz	-38.4	-48		
		f = 5.0GHz	-36 -4			
BW	Bandwidth -3dB			8.4		GHz

# Dynamic Electrical Characteristics for x1+/- x0x+/-

# **Switching Characteristics**

Parameter	Description	Test Conditions	Min.	Тур.	Max.	Units
	Line Eachle Time CEL to set / second	See "Test Circuit for	0.5	15	25	
ι <sub>PZH</sub> , ι <sub>PZL</sub>	Line Enable Time - SEL to XI+/-, XOy+/-	Electrical Characteristics"	0.5	15	25	ns
	Line Dischle Time SEL to vL / vOv./	See "Test Circuit for	0.5	5	25	ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	Line Disable Time - SEL to XI+/-, XOy+/-	Electrical Characteristics"	0.5			
t <sub>PLH</sub>	Propagation Delay, LOW to HIGH	_	17		36	ps
t <sub>PHL</sub>	Propagation Delay, HIGH to LOW	_	21		39	ps
t <sub>b-b</sub>	Bit-to-Bit Skew Within Same Differential	See "Test Circuit for		4	10	
	Pair	Electrical Characteristics"		4	10	ps
t <sub>ch-ch</sub>	Channel to Channel Show	See "Test Circuit for			20	
	Channel-to-Channel Skew	Electrical Characteristics"				ps







5.0Gbps RX Signal Eye Without PI3PCIE3415A





8.0Gbps RX Signal Eye Without PI3PCIE3415A

8.0Gbps RX Signal Eye With PI3PCIE3415A







#### **Differential Insertion Loss**



#### **Differential Return Loss**







#### **Differential Off Isolation**



#### **Differential Crosstalk**

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#### Notes:

- 1.  $C_L$  = Load capacitance: includes jig and probe capacitance.
- 2.  $R_T$  = Termination resistance: should be equal to  $Z_{OUT}$  of the Pulse Generator.
- 3. Output 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
- Output 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. All input impulses are supplied by generators having the following characteristics:  $PRR \le MHz$ ,  $Z_O = 50\Omega$ ,  $t_R \le 2.5ns$ ,  $t_F \le 2.5ns$ .
- 5. The outputs are measured one at a time with one transition per measurement.

#### Switch Positions

Test	Switch
t <sub>PLZ</sub> , t <sub>PZL</sub>	3.0V
t <sub>PHZ</sub> , t <sub>PZH</sub>	GND

## Switching Waveforms



## Voltage Waveforms Enable and Disable Times

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**Differential Insertion Loss and Return Test Circuit** 



Differential Near End Xtalk Test Circuit

# **Part Marking**

ZH Package



YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code



**Differential Off Isolation Test Circuit** 

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# Packaging Mechanical: 42-TQFN (ZH)



For latest package information:

See http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.

## **Ordering Information**

Code	Package Description
	42-contact, Very Thin Quad Flat No-Lead (TQFN), (width 24mm)
	42-contact, Very Thin Quad Flat No-Lead (TQFN), (width 16mm)
	Couc

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm

antimony compounds.

4. E = Pb-free and Green

5. X suffix = Tape/Reel

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